

-60 V

60V P-Channel Enhancement Mode MOSFET

Voltage

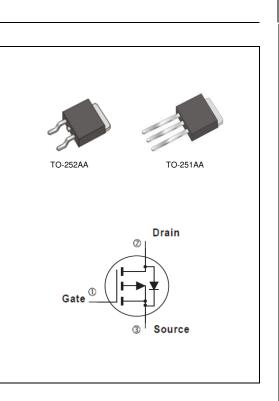
Current -12 A

Features

- $R_{DS(ON)}$, V_{GS} @-10V, I_D @-6A<155m Ω
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : TO-251AA ,TO-252AA Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- TO-251AA Approx. Weight : 0.0104 ounces, 0.297grams
- TO-252AA Approx. Weight : 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMET	ER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	-60	N
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V
Continuous Drain Current	T _C =25°C		-12	
	T _C =100°C	ID	-7.7	А
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	-48	
Power Dissipation	T _C =25°C		50	14/
	$T_{\rm C}=100^{\circ}{\rm C}$	PD	20	W
Continuous Drain Current	T _A =25°C		-2.6	
	T _A =70°C	ID	-2.0	A
Power Dissipation	T _A =25°C		2.0	14/
Power Dissipation	T _A =70°C	PD	1.3	W
Single Pulse Avalanche Energy (Note 6)		E _{AS}	337	mJ
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	$R_{\theta JC}$	2.5	0000
	Junction to Ambient	$R_{ extsf{ heta}JA}$	62.5	°C/W





Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static	1	1	1	•		1
Drain-Source Breakdown Voltage	BV _{DSS}		-60	-	-	v
Gate Threshold Voltage	V _{GS(th)}		-2.0	-2.86	-4.0	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-6A	-	132	155	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =-60V, V_{GS} =0V	-	-	-1.0	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Qg	V _{DS} =-48V, I _D =-12A, V _{GS} =-10V ^(Note 2,3)	-	10.9	-	nC
Gate-Source Charge	Q _{gs}		-	2.7	-	
Gate-Drain Charge	Q _{gd}		-	4.0	-	
Input Capacitance	Ciss	V _{DS} =-25V, V _{GS} =0V, f=1.0MHZ	-	385	-	pF
Output Capacitance	Coss		-	158	-	
Reverse Transfer Capacitance	Crss		-	31	-	
Turn-On Delay Time	td _(on)	V _{DS} =-30V, I _D =-12A, V _{GS} =-10V, R _G =6Ω (Note 2,3)	-	4.4	-	ns
Turn-On Rise Time	t _r		-	59	-	
Turn-Off Delay Time	td _(off)		-	20	-	
Turn-Off Fall Time	t _f		-	36	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	1-		-	-	-12	A
Diode Forward Current	I _S					
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V	-	-0.75	-1	V
Reverse Recovery Time	trr	V _{GS} =0V, I _S =-12A	-	37	-	ns
Reverse Recovery Charge	Qrr	$dI_F/dt=100A/us^{(Note 2)}$	-	67	-	nC

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150$ °C. Ratings are based on low frequency and duty cycles to keep initial $T_J = 25$ °C.
- 4. The maximum current rating is package limited
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
- 6. L=3mH, I_{AS}=-15A, V_{GS}=-10V, V_{DS}=-25V, R_G=25 ohm, Starting T_J=25°C
- 7. Guaranteed by design, not subject to production testing.





PJU12P06 / PJD12P06 **TYPICAL CHARACTERISTIC CURVES** 20 25 V_{G\$}=-20V,-10V V_{DS}=-15V V_{GS}=-8V -I_{DS}-Drain-to-S ource Current(A) -I_{DS}-Drain-to-S ource Current(A) 20 15 15 V_{GS}=-5V 10 10 T_=125°C T_J=25℃ V_{GS}=-4.5V 5 5 V_{GS}=-4V 0 0 0 2 6 8 2 4 6 8 -V_{DS}- Drain-to-Source Voltage(V) 4 0 10 -V_{GS}-Gate-to-Source Voltage(V) Fig.1 On-Region Characteristics **Fig.2 Transfer Characteristics** 180 2.0 R_{Ds}(on)- On-Resistance (Normalized) R_{Ds}(on)- On-Resistance(mΩ) 160 1.7 V_{GS}=-10V, I_D=-6A V_{GS}=-10V 1.4 140 1.1 120 0.8 100 0 25 50 75 100 125 150 175 0 5 10 15 20 Temperature (°C) -I_{DS}-Drain-to-Source Current(A) Fig.3 On-Resistance vs. Drain Current Fig.4 On-Resistance vs. Junction temperature 500 10 I_D=-3A -I_{sD}-Source-to-Drain Current(A) $R_{DS}(on)$ - On-Resistance(m Ω) 400 1 300 T_i=125°C 0.1 T_i=125℃ T₁=25°C 200 T_i=25°C 100 0.01 0 0.3 1.2 2 4 6 8 10 0.6 0.9 -V_{GS}-Gate-to-Source Voltage(V) -V_{SD}-Source-to-Drain Voltage(V) Fig.5 On-Resistance Variation with V_{GS} **Fig.6 Body Diode Characteristics**





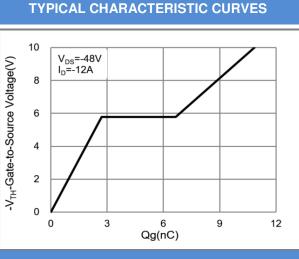


Fig.7 Gate-Charge Characteristics

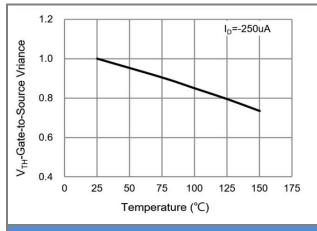
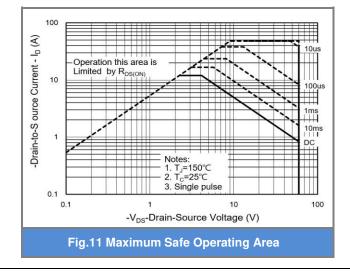
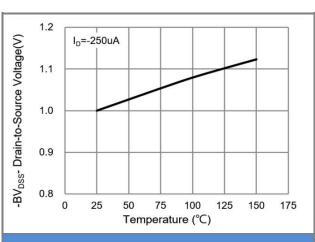


Fig.9 Threshold Voltage Variation with Temperature







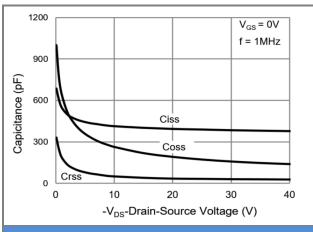


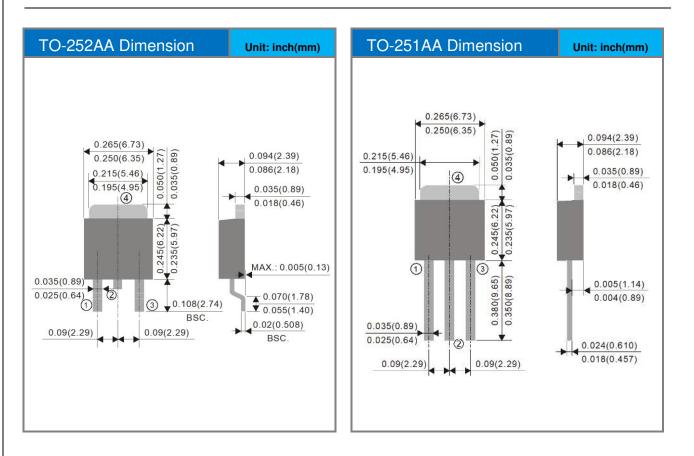
Fig.10 Capacitance vs. Drain-Source Voltage



PJU12P06 / PJD12P06 **TYPICAL CHARACTERISTIC CURVES** $Z_{\text{TH-JC}}$ Normalized Transient Thermal Impedance 1 D=0.5 0.2 0.1 0.1 0.05 0.02 $T_{J,PK} = T_C + P_{DM} * Z_{TH-JC} * R_{TH-JC}$ 0.0 R_{TH-JC} = 2.5 °C/W Single Pulse T_C = 25℃ 0.01 0.0001 0.001 0.1 1 0.01 10 t, Pulse Width PW (s) Fig.12 Normalized Thermal Transient Impedance



Packaging Information



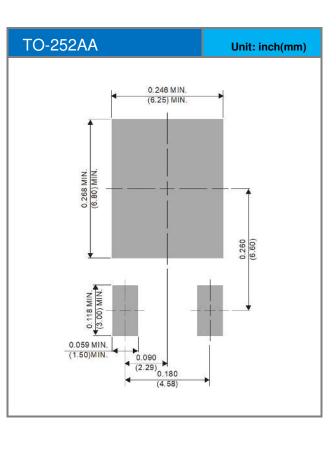




Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJU12P06_T0_00001	TO-251AA	80pcs / Tube	U12P06	Halogen free
PJD12P06_L2_00001	TO-252AA	3,000pcs / 13" reel	D12P06	Halogen free

Mounting Pad Layout





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